

100V N-Channel Power SGT MOSFET

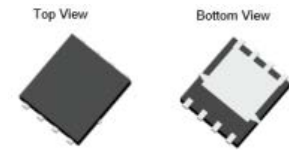
DESCRIPTION :

- Excellent $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- RoHS compliant
- Halogen Free

V_{DSS}	100V
$I_D @ V_{GS}=10V$	54A
$R_{DS(ON_Typ.) @ V_{GS}=10V}$	12.8m Ω

TYPICAL APPLICATIONS :

- Power Management
- Load Switch
- PWM Application



PDFN5x6-8

MAXIMUM RATINGS (at $T_C = 25^\circ C$, unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C=25^\circ C$ $T_C=100^\circ C$	I_D	54 38	A
Pulsed Drain Current ⁽¹⁾		I_{DM}	Refer to Fig4	A
Single Pulsed Avalanche Energy ⁽²⁾		E_{AS}	74	mJ
Power dissipation	$T_C=25^\circ C$ $T_C=100^\circ C$	P_D	94 38	W
Junction & Storage temperature Range		T_J, T_{STG}	-55~+150	$^\circ C$

Notes : 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. EAS condition: Starting $T_J=25^\circ C$, $V_{DD}=50V$, $V_{GS}=10V$, $R_G=25\Omega$, $L=3mH$, $I_{AS}=7A$, $V_{DD}=0V$ during time in avalanche.

THERMAL CHARACTERISTICS

Characteristic	Condition	Symbol	Value	Unit
Thermal resistance,	Junction to Ambient	$R_{\theta JA}$	44	$^\circ C/W$
	Junction to Case	$R_{\theta JC}$	1.3	

ELECTRICAL CHARACTERISTICS (at $T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage VGS = 0V, ID = 250uA	$V_{(BR)DSS}$	100			V
Zero Gate Voltage Drain Current VDS = 80 V, VGS = 0 V	I_{DSS}			1	uA
Gate-Source Leakage Current VGS = ± 20 V, VDS = 0V	I_{GSS}			± 100	nA
Gate-Source threshold voltage VDS = VGS, ID = 250uA	$V_{GS(th)}$	1.2	1.8	2.3	V
Drain-Source On-State Resistance VGS = 10V, ID = 20A VGS = 4.5V, ID = 20A	$R_{DS(on)}$		12.8 18.2	16.7 23.6	m Ω
Input capacitance f=1MHz, VDS= 50 V, VGS=0 V	C_{iss}		969		pF
Output capacitance f=1MHz, VDS= 50 V, VGS=0 V	C_{oss}		329		pF
Reverse transfer capacitance f=1MHz, VDS= 50 V, VGS=0 V	C_{rss}		19		pF
Gate Resistance f=1MHz	R_g		1.5		Ω
Total Gate Charge VDS= 50V, ID= 20A, VGS= 0 to 10V	Q_G		18		nC
Gate to Source Charge VDS= 50V, ID= 20A, VGS= 0 to 10V	Q_{GS}		4		nC
Gate to Drain Charge VDS= 50V, ID= 20A, VGS= 0 to 10V	Q_{GD}		5		nC
Turn-on delay time VDD= 50 V, VGS= 10V, ID= 20A, $R_{GEN}=6.2\Omega$	$t_{d(ON)}$		8		ns
Rise time VDD= 50 V, VGS= 10V, ID= 20A, $R_{GEN}=6.2\Omega$	tr		19		ns
Turn-off delay time VDD= 50 V, VGS= 10V, ID= 20A, $R_{GEN}=6.2\Omega$	$t_{d(OFF)}$		22		ns
Fall time VDD= 50 V, VGS= 10V, ID= 20A, $R_{GEN}=6.2\Omega$	tf		9		ns

Body Diode

ELECTRICAL CHARACTERISTICS (at $T_J = 25\text{ }^\circ\text{C}$, unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Diode Forward Voltage $V_{GS} = 0V, I_S = 20A$	V_{SD}			1.2	V
Maximum Continuous Body Diode Forward Current	I_S			54	A
Maximum Pulsed Body Diode Forward Current	I_{SM}			217	A
Revers Recovery Time $I_F = 20A, di/dt = 100A/\mu s$	T_{rr}		32		ns
Revers Recovery Charge $I_F = 20A, di/dt = 100A/\mu s$	Q_{rr}		30.3		nC

Typical Performance Characteristics

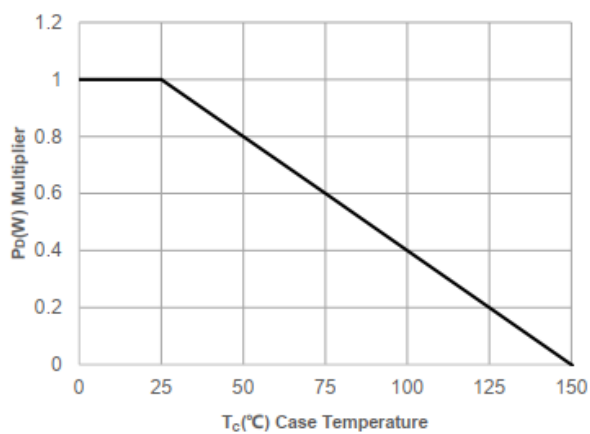


Figure 1. Power De-rating

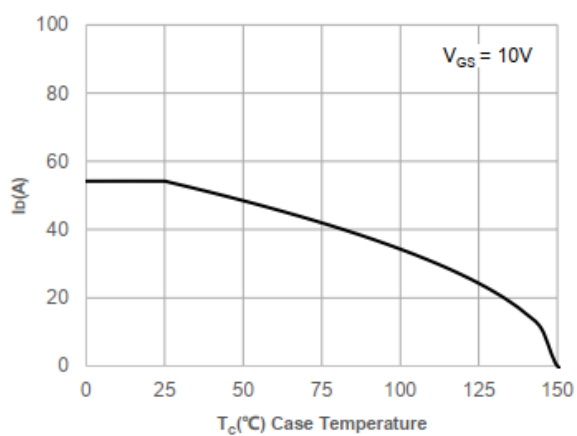


Figure 2. Current De-rating

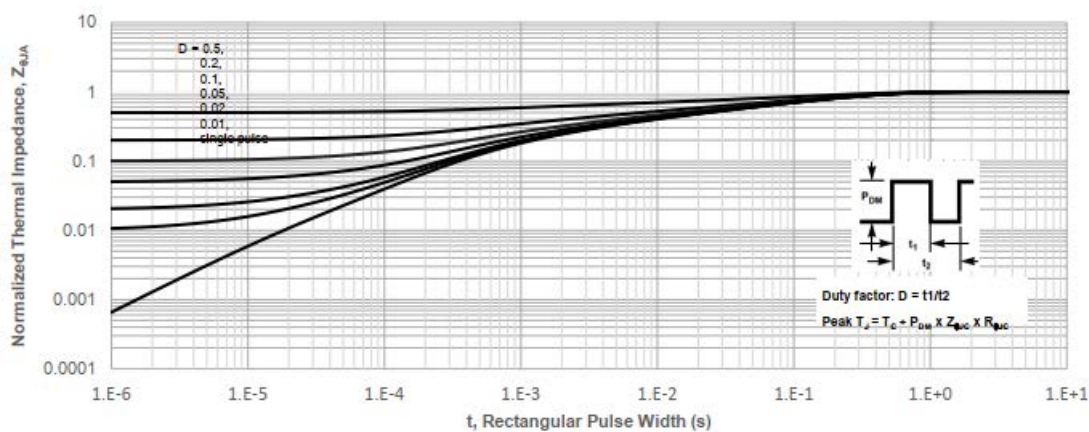


Figure 3. Normalized Maximum Transient Thermal Impedance

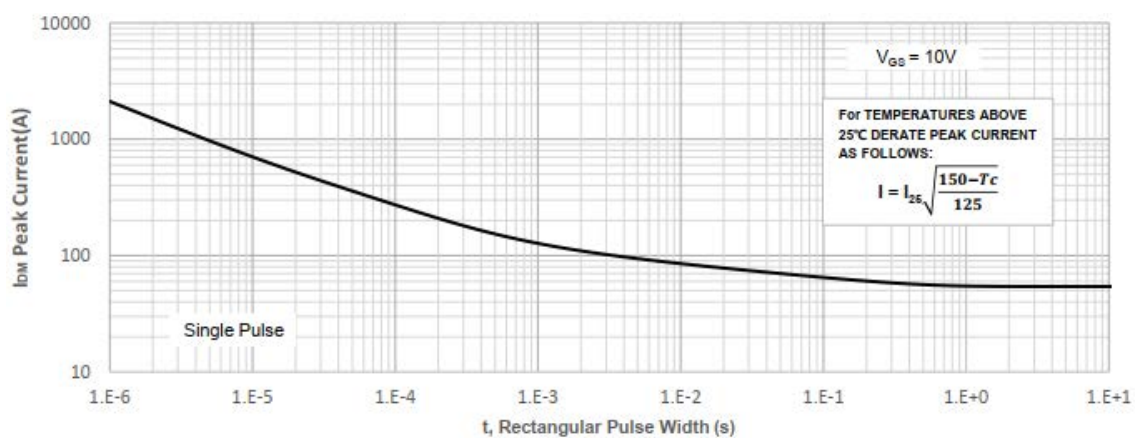


Figure 4. Peak Current Capacity

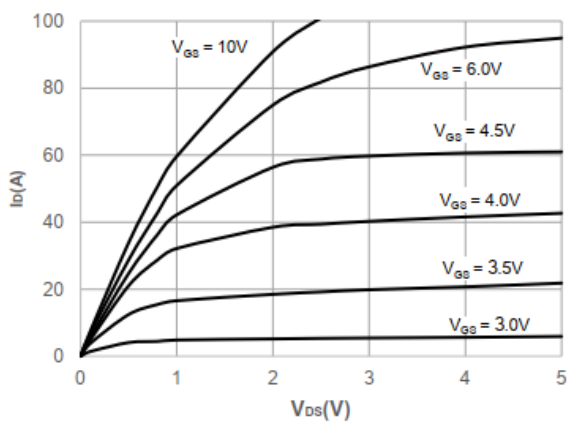


Figure 5. Output Characteristics

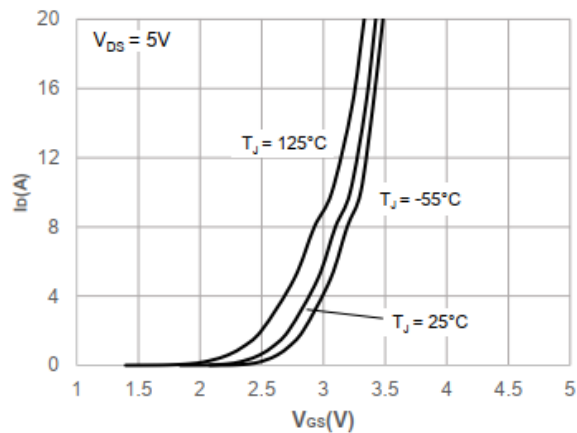


Figure 6. Typical Transfer Characteristics

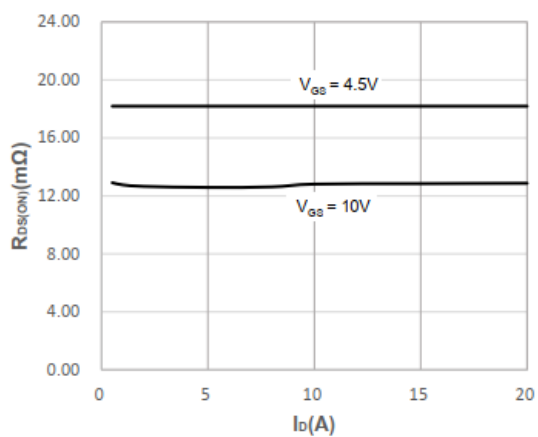


Figure 7. On-resistance vs. Drain Current

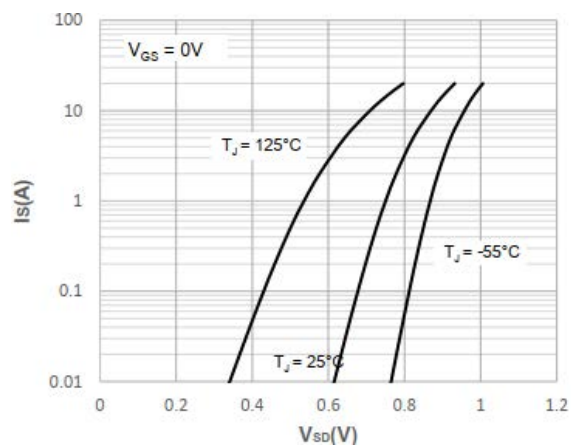


Figure 8. Body Diode Characteristics

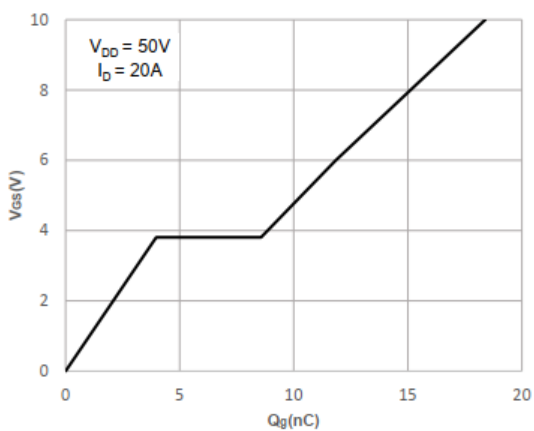


Figure 9. Gate Charge Characteristics

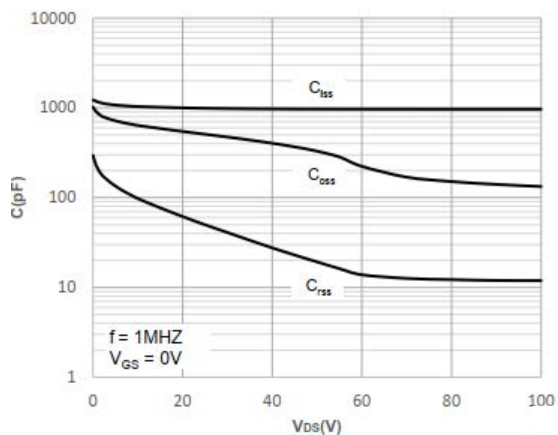


Figure 10. Capacitance Characteristics

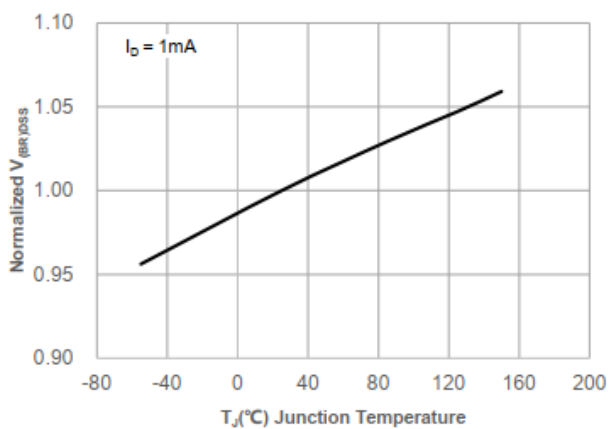


Figure 11. Normalized Breakdown voltage vs. Junction Temperature

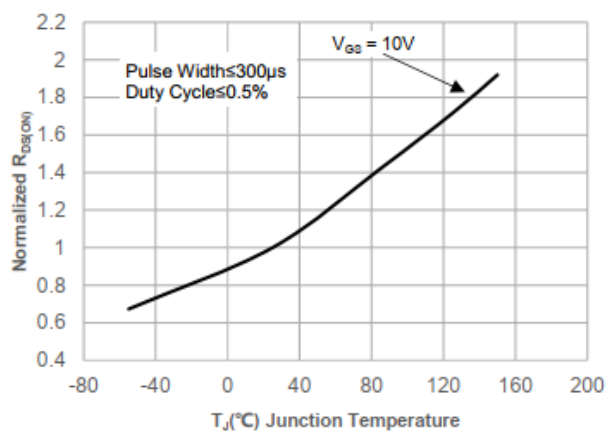


Figure 12. Normalized on Resistance vs. Junction Temperature

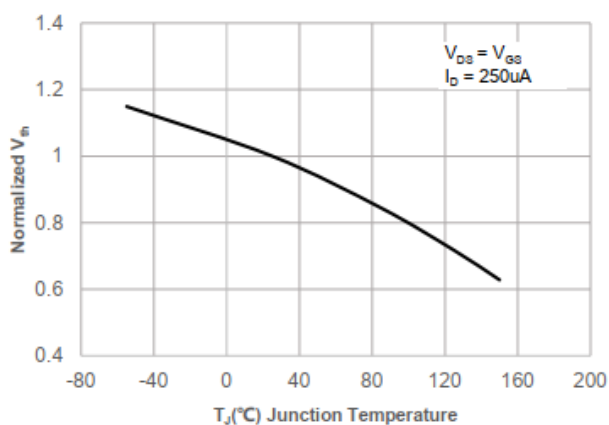


Figure 13. Normalized Threshold Voltage vs. Junction Temperature

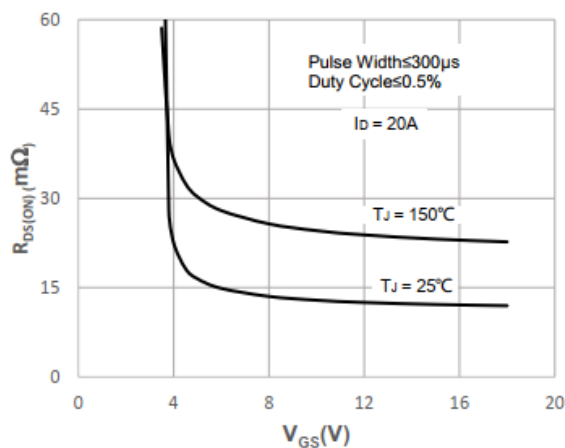


Figure 14. $R_{DS(ON)}$ vs. V_{GS}

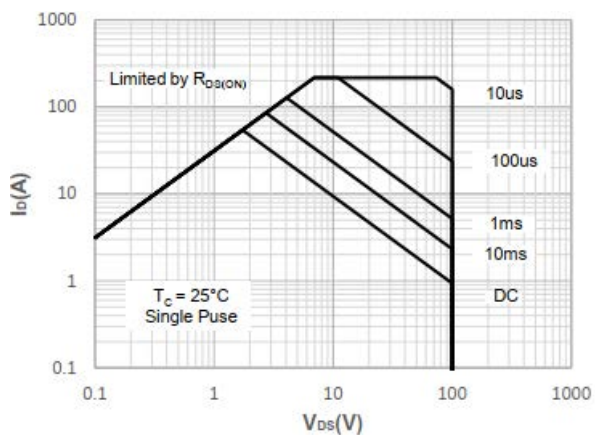
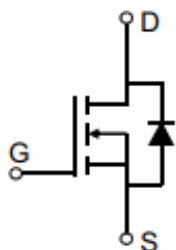
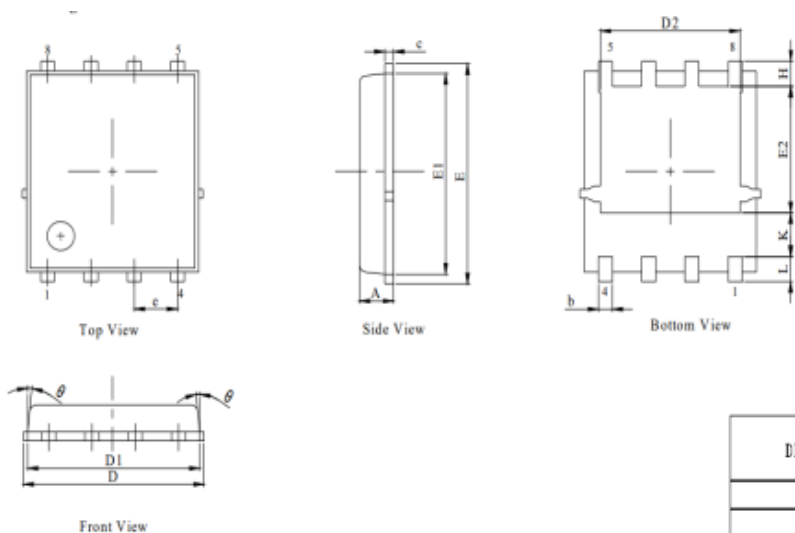


Figure 15. Maximum Safe Operating Area

• Circuit diagram



• Package outlines : Dimensions in (mm)



- NOTES:
1. Dimension and tolerance per ASME Y14.5M, 1994.
 2. All dimensions in millimeter (angle in degree).
 3. Dimensions D1 and E1 do not include mold flash protrusions or gate burrs.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.9	1	1.15
b	0.31	0.41	0.51
C	0.24	0.32	0.4
D	5	5.2	5.4
D1	4.95	5.05	5.15
D2	4	4.1	4.2
E	6.05	6.15	6.25
E1	5.5	5.6	5.7
E2	3.42	3.53	3.63
e	1.27BSC		
H	0.6	0.7	0.8
L	0.5	0.7	0.8
K	1.23 REF		
0			10

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